



제25회 한국반도체학술대회

The 25th Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 16:15-17:30

Room F (봉래, 6층)

F. Silicon and Group-IV Devices and Integration Technology **분과**

[WF4-F] Steep-Slope II : NC-FET

WF4-F-1 16:15-16:30	Use of Negative Capacitance to Lower the Switching Voltage of Nanoelectromechanical Relay Kihun Choe, Wonseok Lee, and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>
WF4-F-2 16:30-16:45	Impact of Ferroelectric Capacitor's Electrode Area on the Performance of Negative (Differential) Capacitance Field Effect Transistor Hyunki Cho, Jaemin Shin, and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>
WF4-F-3 16:45-17:00	Tunnel Field Effect Transistor with Ferroelectric Gate Dielectric Kitae Lee ¹ , Junil Lee ¹ , Ryoongbin Lee ¹ , Euyhwan Park ¹ , Sihyun Kim ¹ , Hyun-Min Kim ¹ , Sangwan Kim ² , and Byung-Gook Park ¹ <i>¹Department of Electrical and Computer Engineering, Seoul National University, ²Department of Electrical and Computer Engineering, Ajou University</i>
WF4-F-4 17:00-17:15	Steep Slope Silicon-on-Insulator FET with Negative Capacitance Eunah Ko and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>
WF4-F-5 17:15-17:30	Transient Response of Polarization Switching in PZT Ferroelectric Capacitor Hansol Ku and Changhwan Shin <i>Department of Electrical and Computer Engineering, University of Seoul</i>